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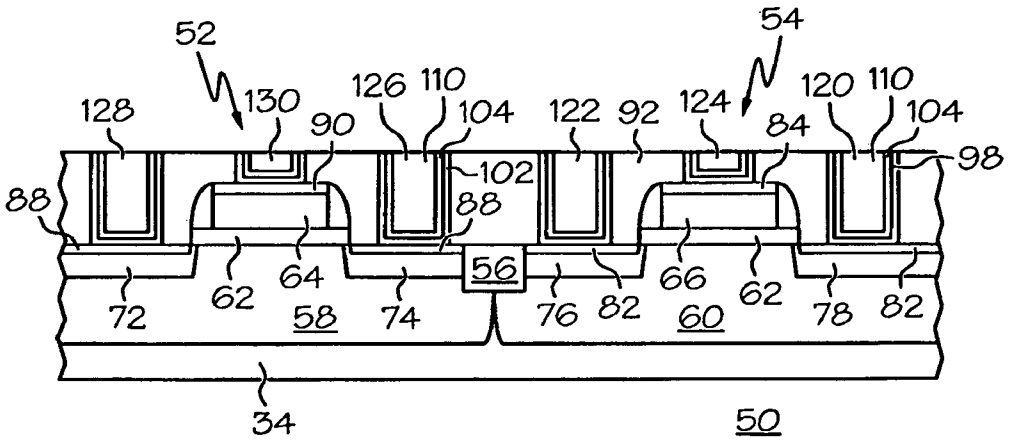
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(54) **Title:** LOW CONTACT RESISTANCE CMOS CIRCUITS AND METHODS FOR THEIR FABRICATION



(57) **Abstract:** A low contact resistance CMOS integrated circuit [50] and method for its fabrication are provided. The CMOS integrated circuit [50] comprises a first transition metal [102] electrically coupled to the N-type circuit regions [72, 74] and a second transition metal [98] different than the first transition metal electrically coupled to the P-type circuit regions [76, 78]. A conductive barrier layer [104] overlies each of the first transition metal and the second transition metal and a plug metal [110] overlies the conductive barrier layer.

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